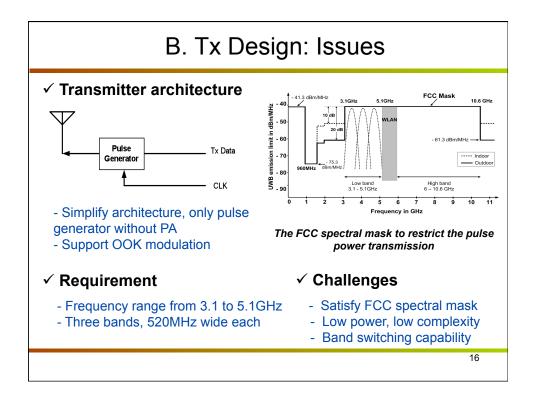
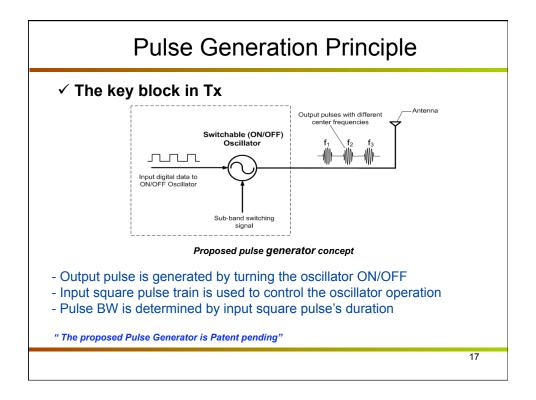
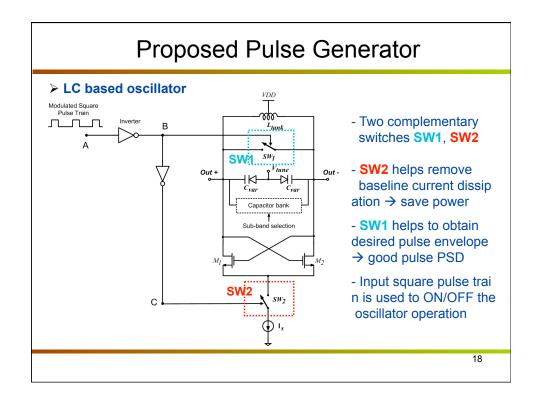
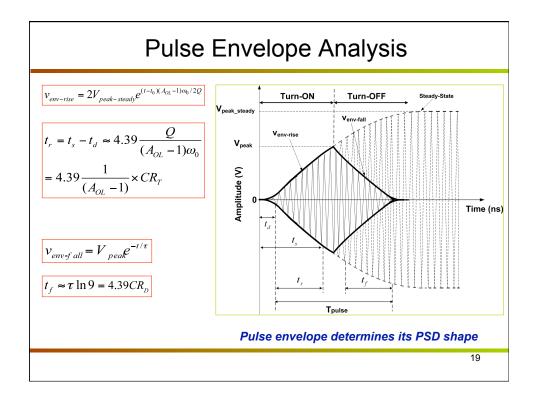


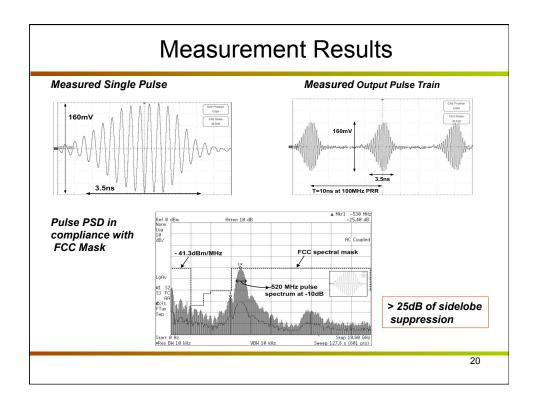
	Specifications	Unit	Target	Condition
System	Frequency	GHz	3.1 ~ 5	Low UWB band
	Bandwidth	MHz	528	@ -10dB BW
	PRF	MHz	16	Variable
	Power Supply	V	1.5	TSMC 0.18um
Тх	Output Power	dBm	1.1	Peak Power
	Amplitude	mV	150-200mV	
	Pulse Width	ns	3~4	Real duration
Rx	NF	dB	12~14	
	Gain	dB	36 ~ 60	-30dBm @ Squarer Inpu

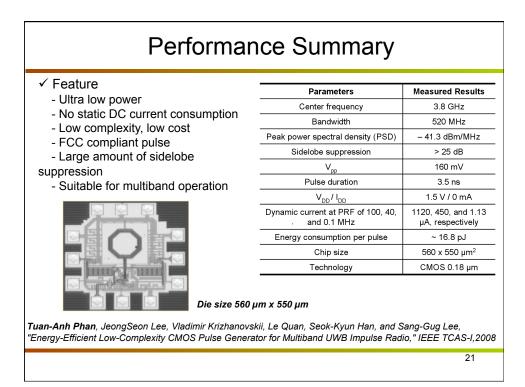


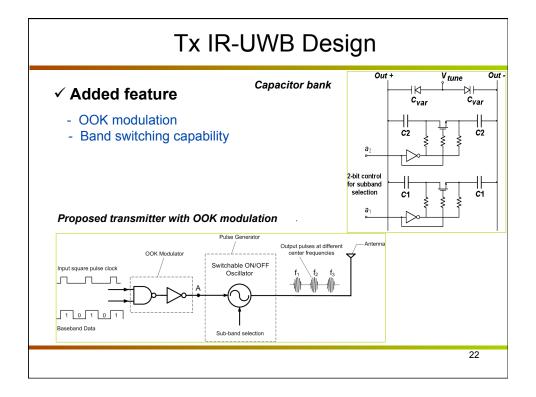


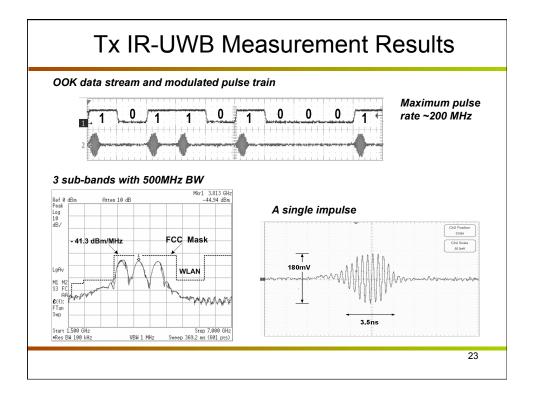




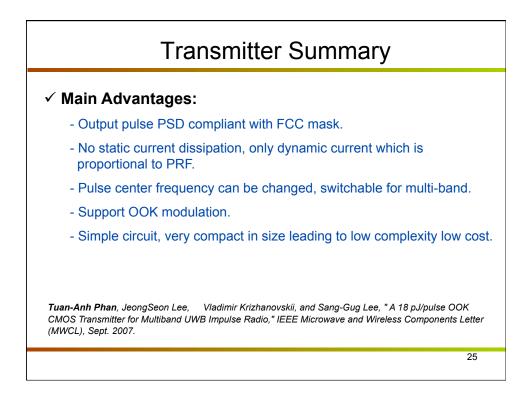


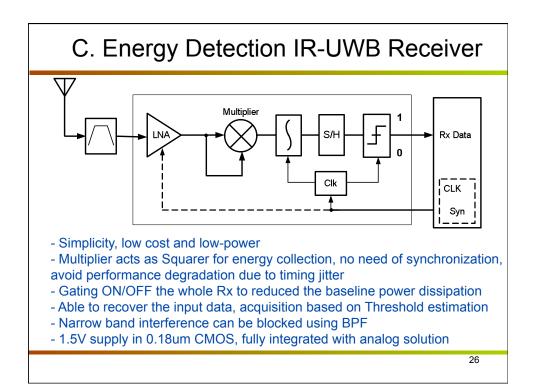


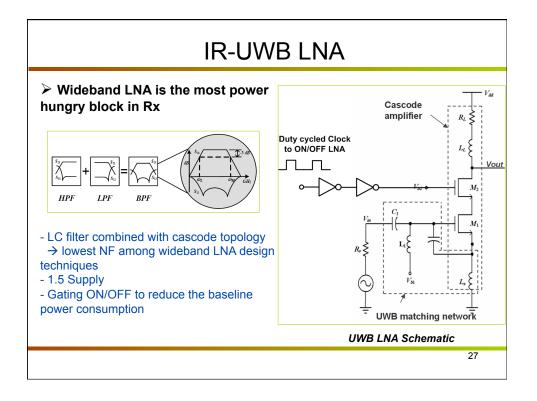


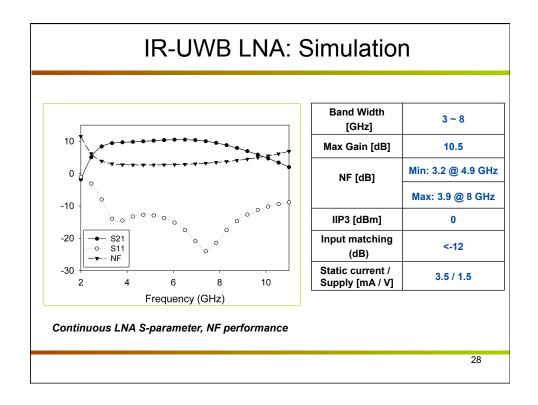


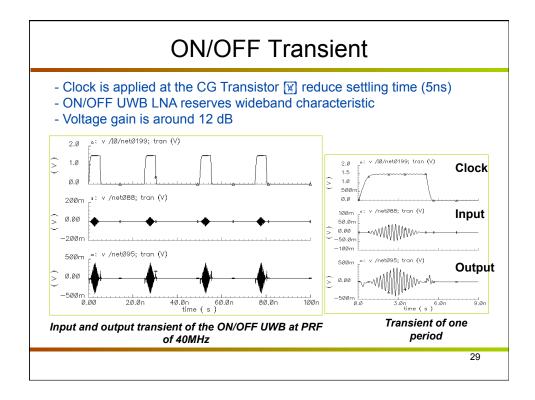
Parameters	Measured Results	
Sub-band center frequencies	3.2, 3.8, and 4.4 GHz	
Bandwidth	520 MHz	
Peak power spectral density (PSD)	– 41.3 dBm/MHz	
Maximum sidelobe suppression	> 20 dB	
V _{pp}	180 mV	
Pulse duration	3.5 ns	
Dynamic current at PRF of 0.1, 40 , and 100 MHz	1.2, 486, and 1215 μ A, respectively.	Core die size 580 x 680 µm
Energy consumption per pulse	~ 18 pJ	
V _{DD}	1.5 V	-
Chip size	580 x 680 µm²	
Technology	CMOS 0.18-µm	

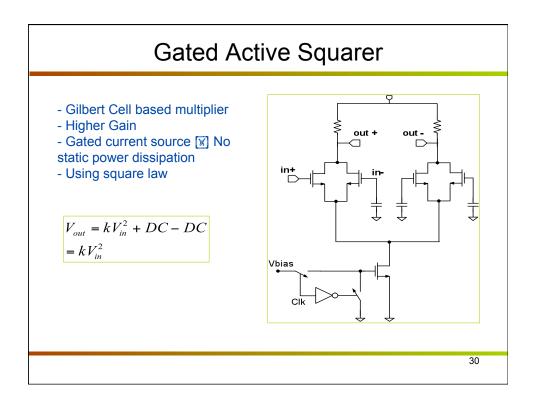


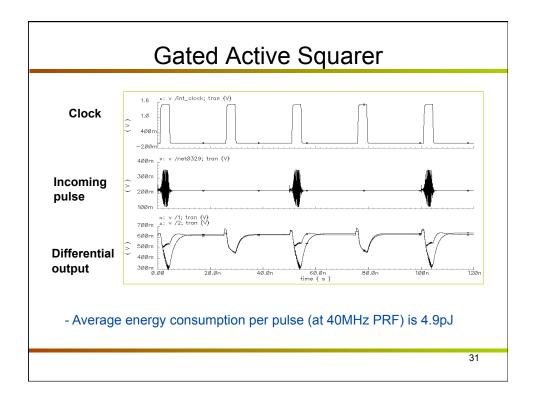


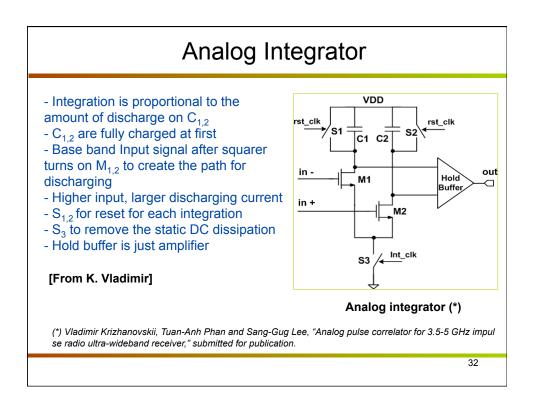


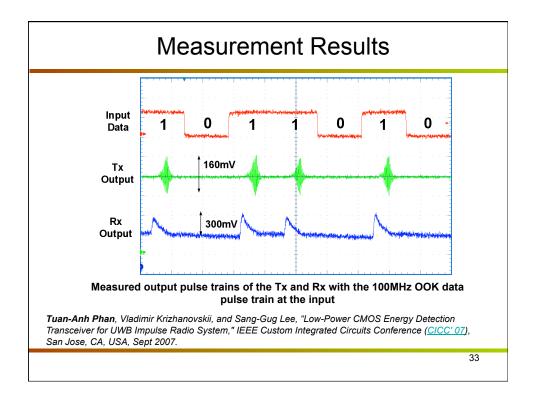


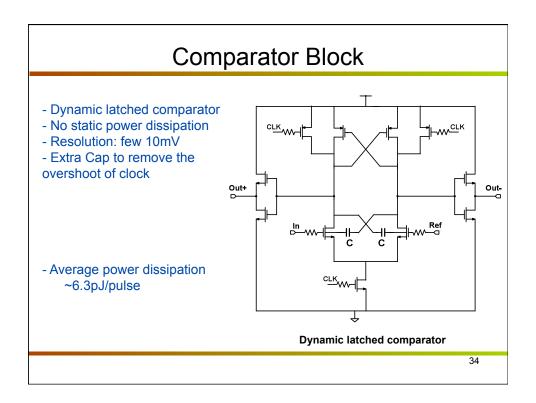


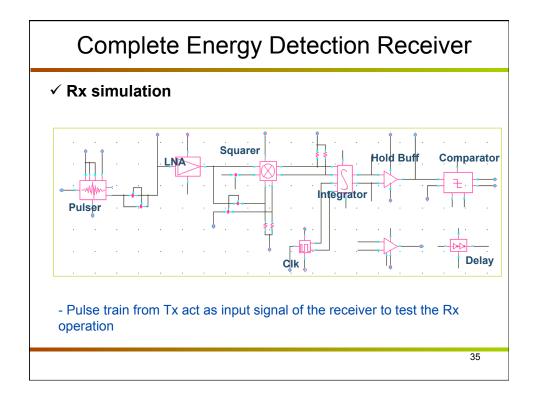


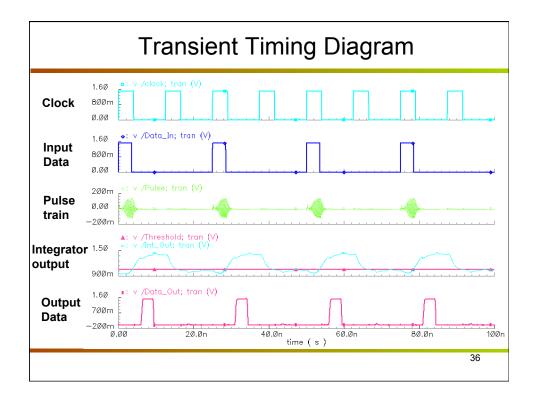


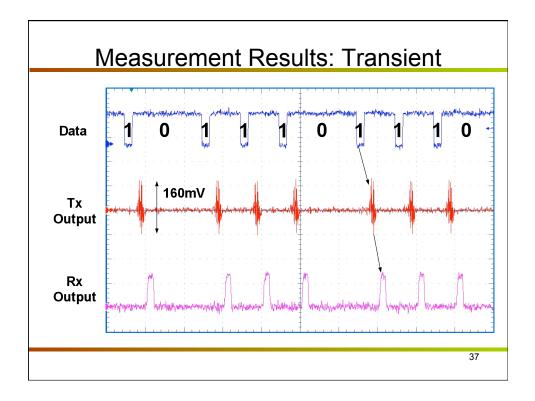


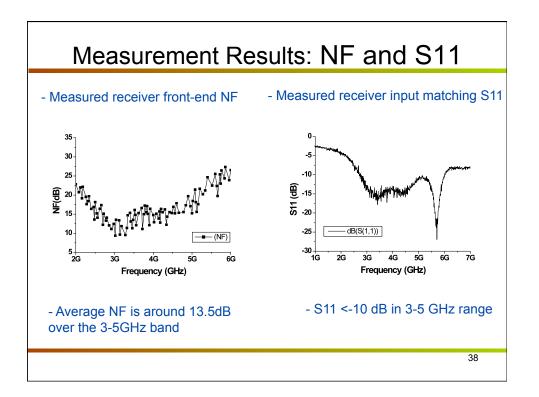


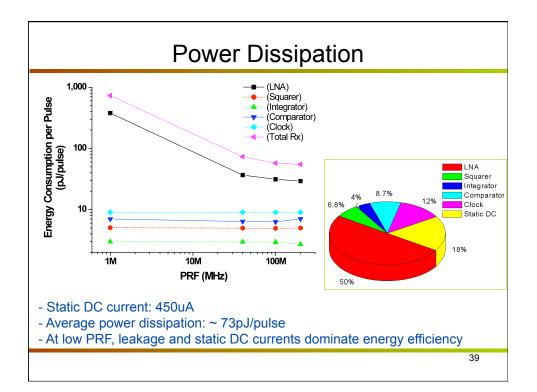












Performance Summary					
Parameters	Measurement Results				
Operation frequency range	3-5 GHz				
Subband bandwidth / Center Freq	528 MHz / 3.8 GHz				
Min detectable input	– 60 dBm (Sim)				
S11	< -10 dB in 3-5 GHz band				
NF	~ 13.5 dB				
Dynamic power dissipation	~73 pJ/pulse				
Static DC current consumption	450 µA				
V _{DD}	1.5 V				
Core chip size	1.3 mm ²				
Technology	CMOS 0.18-µm				
		Chip photo of the Tx/Rx, 1.1 x 1.5 mn			

